

03 The passivation films [15] 12 and 18 of PSG are formed on the top surface, and electrode contact portions are etched (FIG. 10).

IN THE CLAIMS

Please amend Claims 1 and 12 as follows:

1. (Amended) A semiconductor device comprising:

a first semiconductor layer of a first conductivity type having first and second major surfaces;

a first semiconductor region of a second conductivity type formed selectively in said first major surface of said first semiconductor layer so that said first semiconductor layer is exposed in a peripheral portion of said first major surface and said first semiconductor layer is exposed in the form of an insular region in a central portion of said first major surface;

03 a second semiconductor region of the first conductivity type formed in a surface of said first semiconductor region, with a channel region provided between said second semiconductor region and said insular region of said first semiconductor layer;

a gate insulating film formed on a surface of said channel region;

a first gate formed on said gate insulating film;

an interlayer insulating film formed at least on said first gate:

a first main electrode formed over a surface of said interlayer insulating film and covering a surface of said second semiconductor region, said first main electrode being electrically connected to said second semiconductor region and having an end extending to a boundary between the peripheral portion of said first major surface and the central portion of said first major surface;

a second main electrode formed on said second major surface of said first semiconductor layer; and

A well
an integral semi-insulating plasma CVD nitride film covering at least the peripheral portion of said first major surface other than the central portion of said first major surface and not extending [to] beyond an upper portion of said first gate, said integral semi-insulating plasma CVD nitride film having a conductivity which does not lose function as an insulating film and stabilizes breakdown voltage characteristics of the semiconductor device.

12. (Amended) A semiconductor device comprising:

a first semiconductor layer of a first conductivity type having first and second major surfaces;

25
at least one first semiconductor region of a second conductivity type formed selectively in said first major surface of said first semiconductor layer so that said first semiconductor layer is exposed in a peripheral portion of said first major surface and said first semiconductor layer is exposed in the form of a plurality of insular regions in a central portion of said first major surface;

a plurality of second semiconductor regions of the first conductivity type formed in a surface of said at least one first semiconductor region, with channel regions provided between said second semiconductor regions and said insular regions of said first semiconductor layer;

a gate insulating film formed on a surface of said channel regions;

a first gate formed on said gate insulating film;

an interlayer insulating film formed at least on said first gate[:];

a first main electrode formed over a surface of said interlayer insulating film and covering a surface of said second semiconductor region, said first main electrode being